Technical Data

DIODE

DISCRETE SEMICONDUCTOR
INDUSTRIES

maximum ratings

Voltage, Reverse (VR)	600.0	V
Voltage, Reverse Peak (VRM)	600.0	V
Current at VR = OV (IO)		A
Current Average Rectified (IF)	1.0	A
Current Surge Peak (IFM)		A
Current, Surge (IFM) at tp = 10 ms	50.0	A
Max. Power Dissipation (PT) at TC = 25 °C		W
Max. Thermal Resistance (Rth J-A)	50.0	°C/W
Max. Junction Temperature (TJ)	200.0	°C

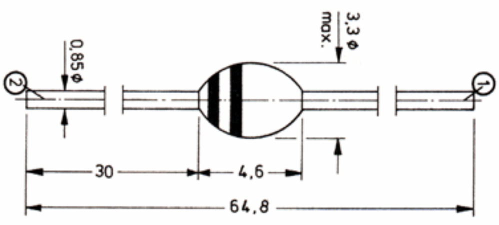
NO.	1N5618-M
TYPE	SILICON
	RECTIFIER
CASE	SOD-57
	MIL-S-19500
	BURN-IN 48h/125°C

PERFORMANCE CHARACTERISTICS at T_C = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	VF	IF = 1.0 A (1)	-	1.2	V
2.	IR	VR =600.0 V	-	0.5	µA
3.	IR	VR = 600.0 V, TA = 100.0 °C	-	25.0	µA
4.	trr	IF = 0.5 A, IR = 1.0 A, irr = 0.25 A	-	2.0	µs
5.	CT	VR = 12.0 V, f = 1.0 MHz	-	50.0	pF
6.					
7.					
8.					
9.					
10.					
11.					
12.					
13.					
14.					
15.					
16.					
17.					
18.					
19.					
20.					

Notes (1)pulse-tested tp ≤ 300 µs, duty cycle ≤ 2 %

DIMENSIONS
in mm



Marking 5618-M+GREEN DOT

Customer GENERAL PURPOSE